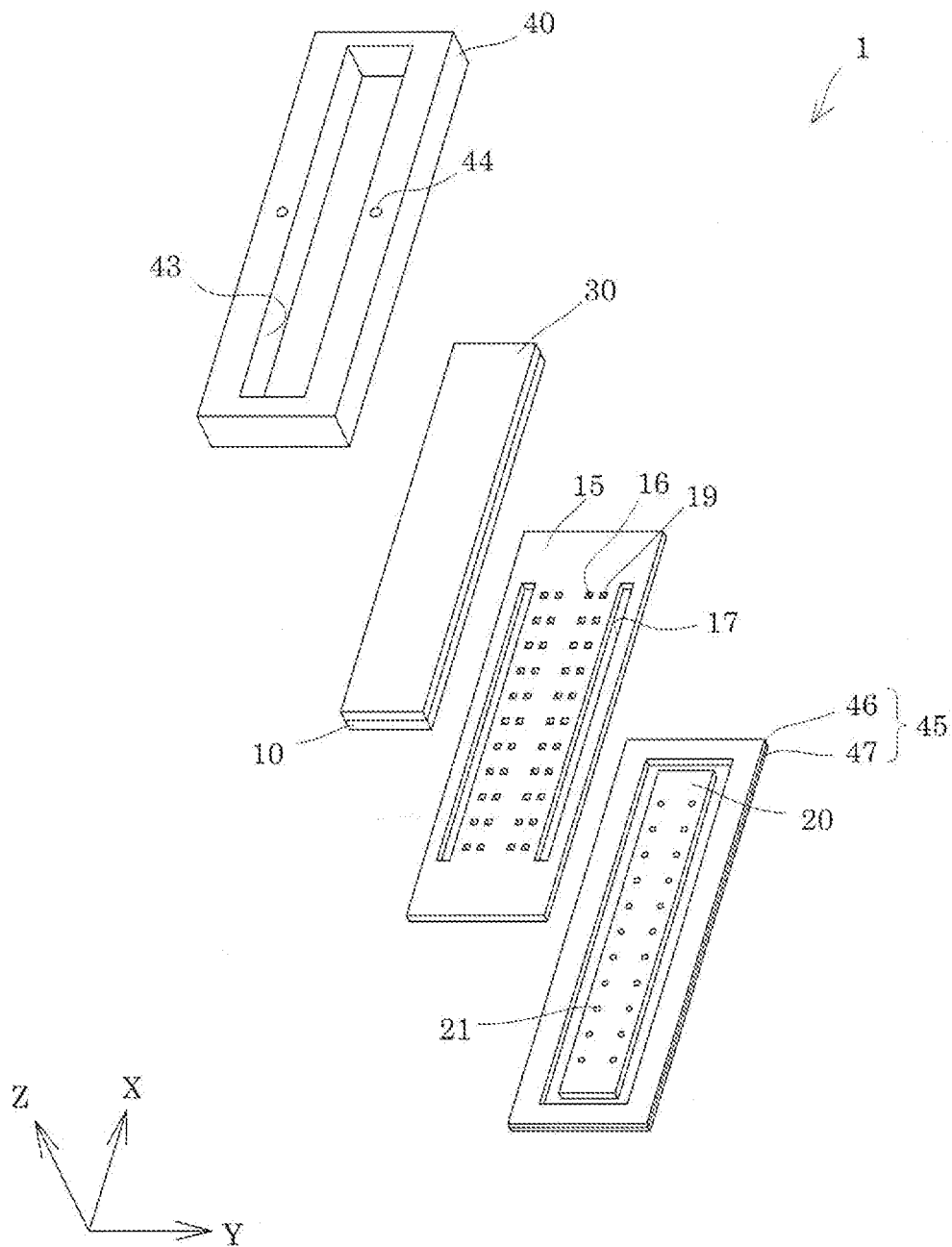
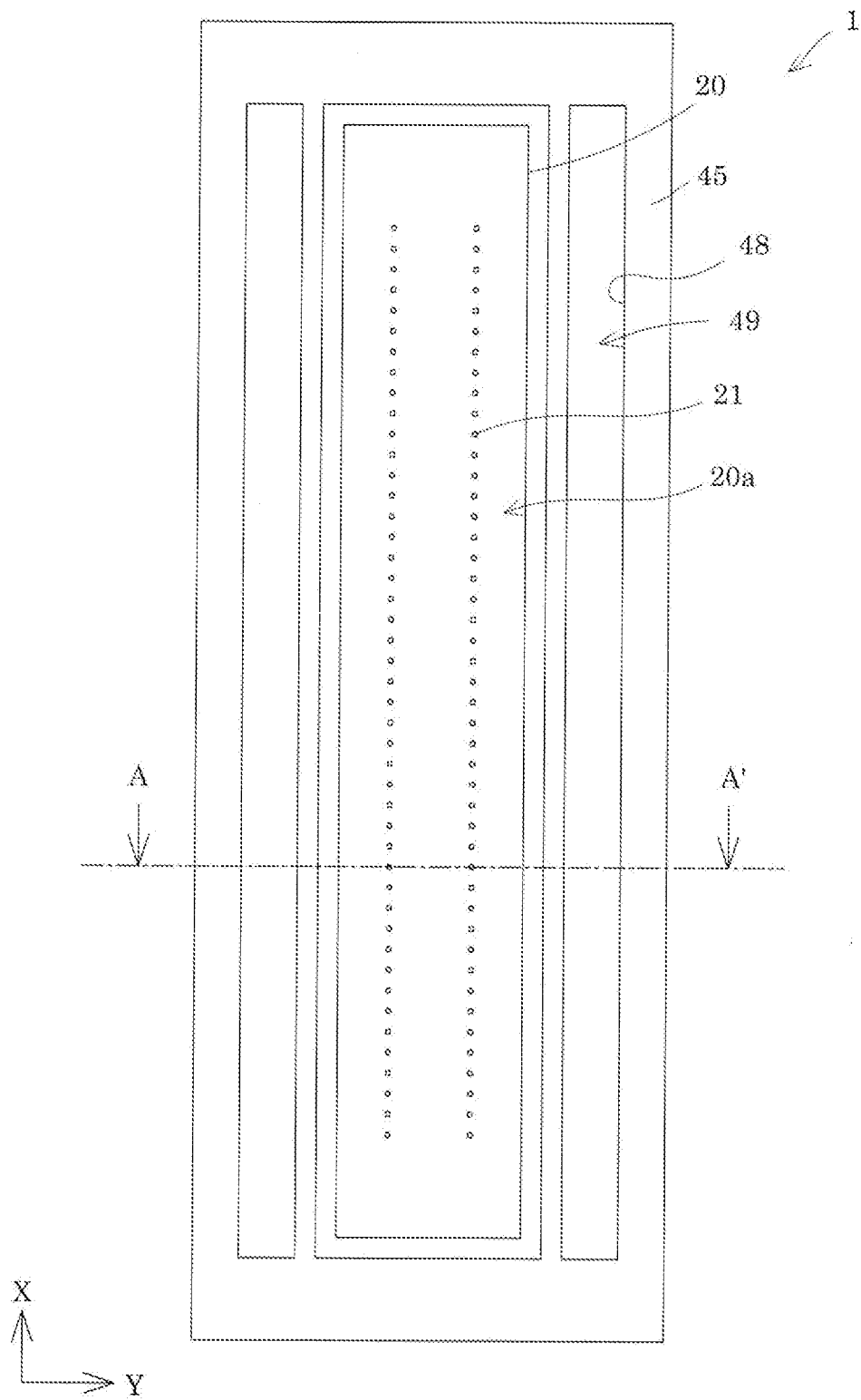


[Fig. 1]



[Fig. 2]

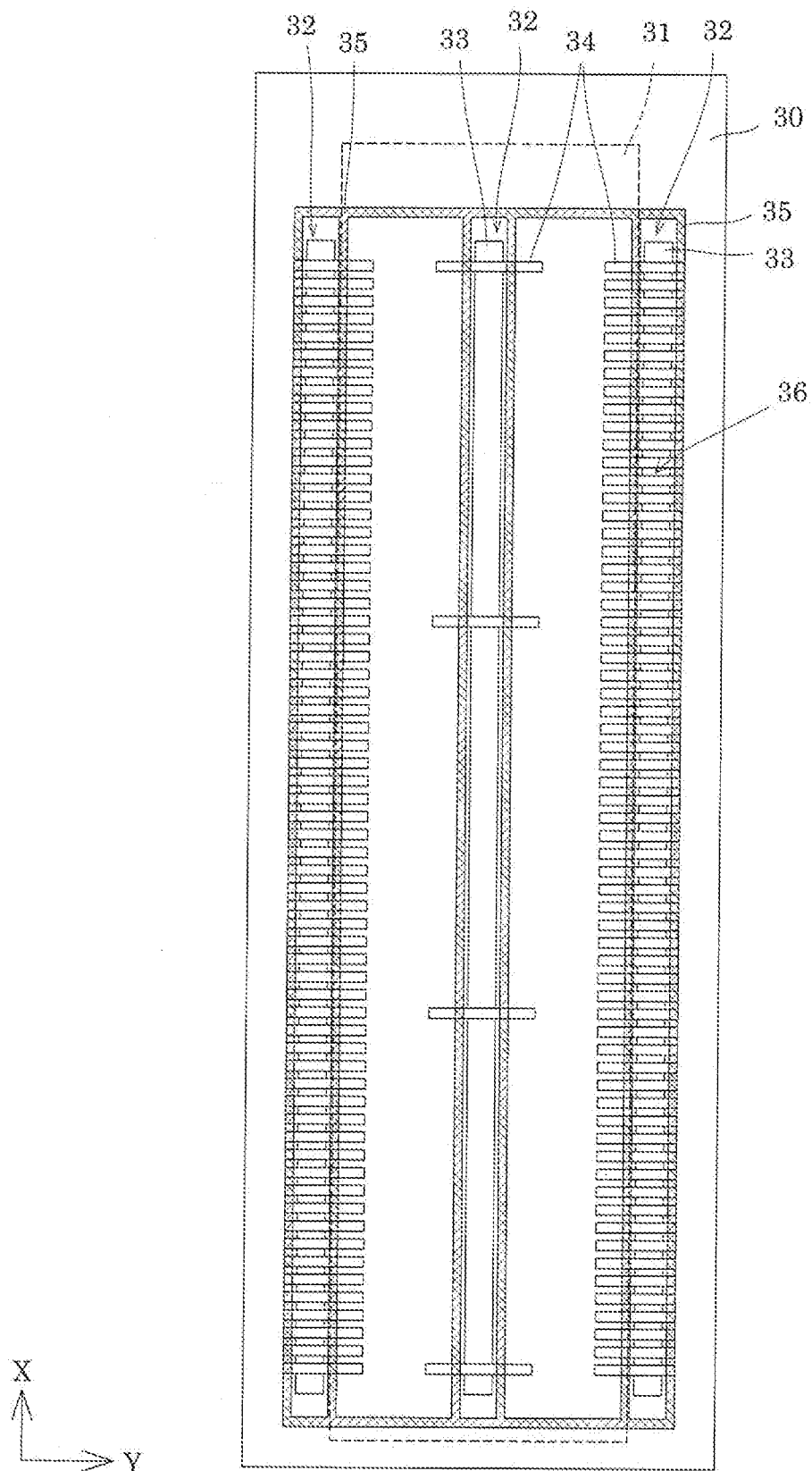




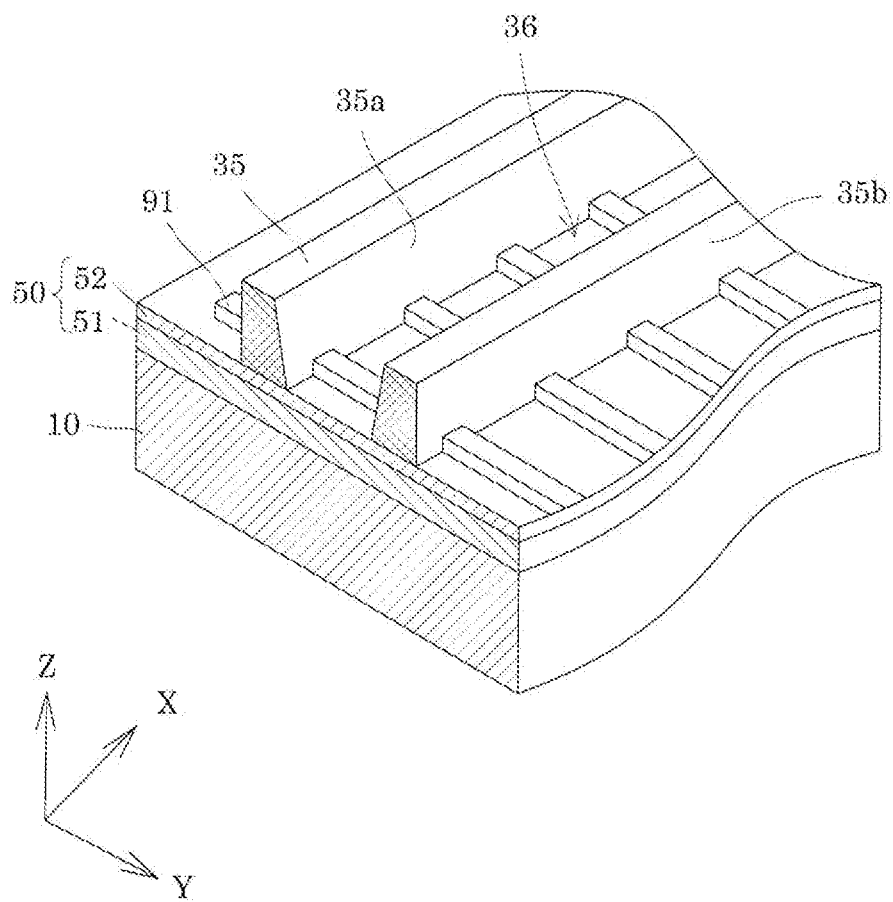




[Fig. 6]

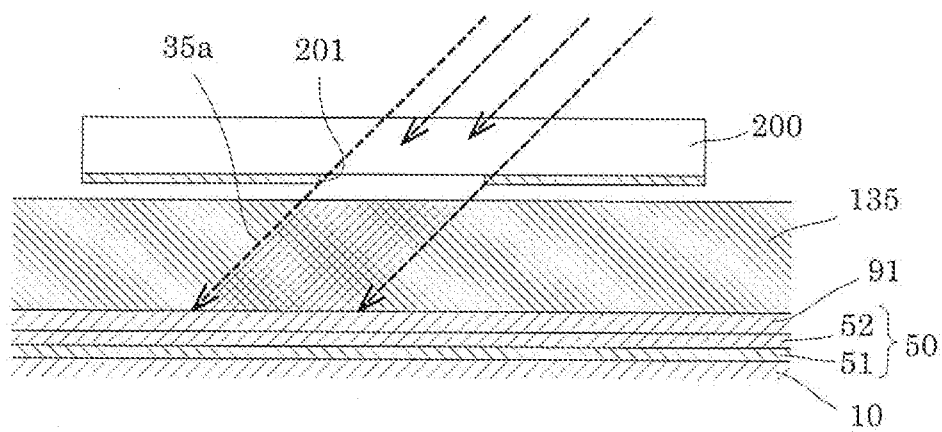


[Fig. 7]

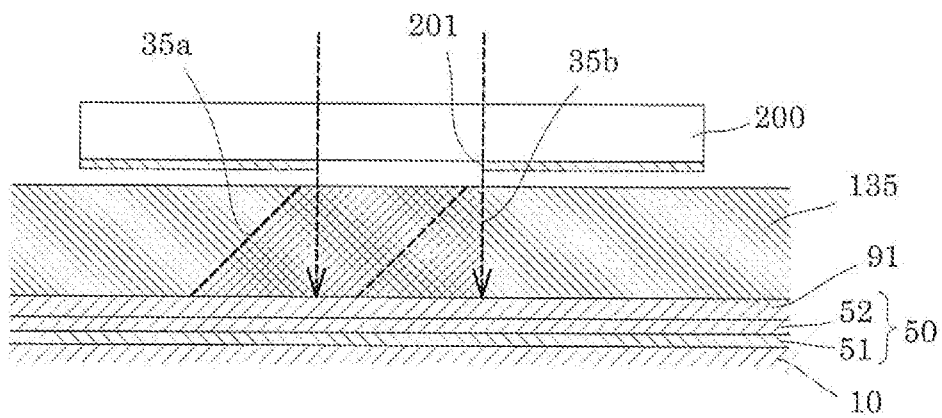




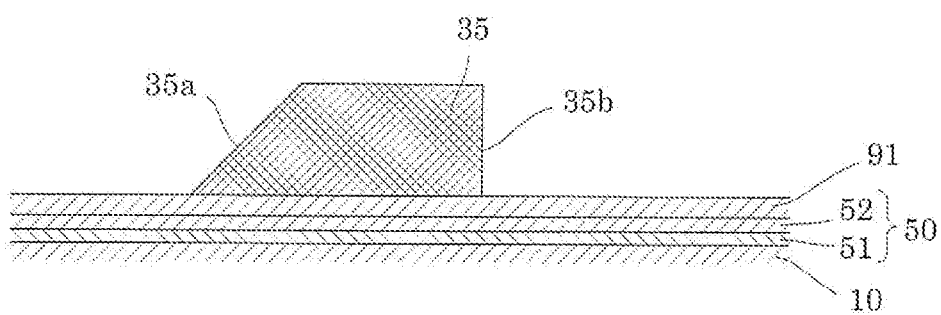
[Fig. 9A]



[Fig. 9B]



[Fig. 9C]



This cross-sectional diagram illustrates a multi-layered semiconductor device. The top layer is labeled 40. Below it is a layer 30 containing several rectangular features 91. A horizontal layer 35 is positioned above these features. Beneath layer 35 are two sets of U-shaped structures, each consisting of a central part 52 and side parts 51. Below these are layers 10 and 15. Layer 15 contains large rectangular openings or cavities. At the bottom, there is a complex structure involving layers 46 and 47, which form part of a larger assembly 45. This assembly includes various components like 49, 18, 34, 33, 35, 12, 19, 20, 21, 16, and 20a. A coordinate system at the bottom left shows the Z-axis pointing upwards and the Y-axis pointing to the right.

[Fig. 11]

